MN74HC367/MN74HC367S

Hex TRI-STATE Buffers

Outline

The MN74HC367/MN74HC367S consists of high speed non-inverting buffer having 3-state outputs.

Because of the large current outputs, these buffers assure high speed operation even when driving a large capacity bus line. They have two inputs $\overline{G}1$ and $\overline{G}2$ to enable the outputs when the level is "L", and the input $\overline{G}1$ controls four gates while the input $\overline{G}2$ controls two gates.

Owing to the silicon gate CMOS process, these buffers have realized low power consumption and high noise immunity equivalent to those of a standard CMOS and the operation speed as high as of an LS TTL, and can directly drive fifteen LS TTL inputs.

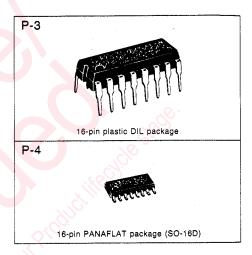
To protect the input and output against electrostatic breakdown, a resistor and a diode are used for the V_{cc} and the GND. The pin configuration and the function are the same as those of the standard 54LS/74LS logic family.

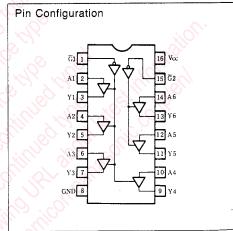
■ Truth Table

	Output	
$\overline{\overline{G}}$	A	YS
Н	· ×	Hi-Z
L	Н	LOH CO
L	L	9/1 FO X

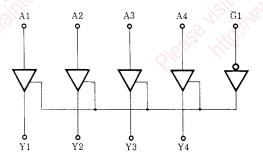
Note 1. Hiz : High impedance

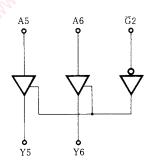
2. × : "H" or "L" either will do.





■ Logic Diagram





■ Absolute Maximum Ratings

Item			Symbol	Rating	Unit		
Supply voltage			Vcc	-0.5~+7.0	V		
Input output voltage			V _I , V _O	$-0.5 \sim V_{cc} + 0.5$	V		
Input protective diode current		I_{iK}	±20	mA			
Output parasitic diode current		I _{ok}	±20	mA			
Output current		I_{O}	±35	mA			
Supply current		Icc, I _{GND}	±70	mA			
Storage temperature		$T_{ m stg}$	−65 ~ +150	°C			
	MN74HC367	$Ta = -40 \sim +60 ^{\circ}C$	P_{D}	400	mW		
Power	WIN7411C307	$Ta = +60 \sim +85^{\circ}C$	Гр	Decrease to 200mW at the rate of 8mW/°C			
dissipation	MN74HC367S	$Ta = -40 \sim +60 ^{\circ}C$	P_{D}	275	mW		
	MINTARCSOTS	$Ta = +60 \sim +85^{\circ}C$	£,D	Decrease to 200mW at the rate of 3.8mW/°C			

■ Recommended Operating Conditions

Item	Symbol	V _{cc} (V)	Rating	Unit	
Operating power supply voltage	Vcc		1.4~6.0	V	
Input output voltage	$V_{\mathfrak{b}} V_{\mathfrak{o}}$		0~Vcc	V	
Operating temperature	T _A		-40~+85	°C	
		2.0	0~1000	ns	
Input rise, fall time	t _r , t _f	4.5	0~500	ns	
		6.0	0~400	ns	

■ DC Characteristics (GND=0V)

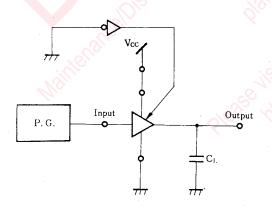
	Symbol	V	Test Condition			Temperature					D.
Item		V _{cc} (V)	Vı	Vo Unit	Ta=25°C			Ta=-40~+85°C		Unit	
					Unit	min.	typ.	max.	min.	max.	
		2.0		1,0	100	1.5	00	Q,	1.5	0:	_
Input voltage high level	V_{IH}	4.5		W. 4	(0)	3.15		100	3.15	0.17	V
		6.0		6	· xO	4.2	1 9	12.11	4.2	0	
		2.0	62	100	de	~CO.	10	0.3		0.3	
Input voltage low level	V_{1L}	4.5	2	b. 4		12 1	100	0.9	5	0.9	V
		6.0	1			-01		1.2	.0	1.2	
	·.c	2.0		-20.0	μΑ	1.9	2.0	100	1.9		
		4.5	V_{IH}	-20.0	μ_{A}	4.4	4.5	2//	4.4		
Output voltage high level	V _{OH}	6.0	or	-20.0	μ A	5.9	6.0		5.9		V
		4.5	V_{IL}	-6.0	mA 💉	3.92	.0)		3.84		
202	10	6.0		-7.8	mA	5.48	?		5.34		
		2.0		20.0	μΑ	11/1	0.0	0.1		0.1	
		4.5	V_{IH}	20.0	μ A	12	0.0	0.1		0.1	
Output voltage low level	Vol	6.0	or	20.0	μ A		0.0	0.1		0.1	V
•		4.5	V _{IL}	6.0	mA			0.26		0.33	
		6.0		7.8	mA			0.26		0.33	
Input leakage current	I_{i}	6.0	V _I =V _{CC} or GND				±0.1		±1.0	μΑ	
3-state output OFF leakage current	I _{OZ}	6.0	V _I =V _{IH} or V _{IL} V _O =V _{CC} or GND)			±0.5		±5.0	μΑ
Static supply current	Icc	6.0	$V_I = V_{CC}$ or GND, $I_O = 0$		$I_0 = 0$			8.0		80.0	μΑ

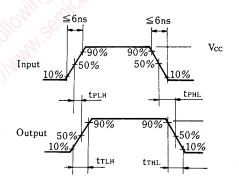
■ AC Characteristics (GND=0V, Input transition time ≤6ns, C_L=50pF)

		V _{cc} (V)	Test Condition	Temperature					
Item	Symbol			,	Ta=25°0	2	Ta=-40	Unit	
				min.	typ.	max.	min.	max.	
·		2.0			13	75		95	
Output rise time	t _{TLH}	4.5			6	15		19	ns
		6.0			5	13		16	
		2.0			11	75		95	
Output fall time	t _{THL}	4.5			4	15		19	ns
		6.0			4	13		16	
D		2.0		1	12	75		95	
Propagation time	t _{PLH}	4.5			7	15	_(0	19	ns
(L→H)		6.0			6	13	100	16	
n		2.0			11	75	5	95	•
Propagation time	t _{PHL}	4.5			6	15	0	19	ns
(H→L)		6.0			5	13		16	
0 -4-4		2.0			17	100		125	
3-state propagation time	t _{PHZ}	4.5	$R_L=1k\Omega$		13	20		25	ns
(H→Z)		6.0			12	17		17	
0		2.0		20	18	100		125	
3-state propagation time	t _{PLZ}	4.5	$R_L = 1k\Omega$		11	20		25	ns
(L→Z)		6.0		0),	10	17		17	
		2.0	0.	1	17	75		95 🦱	
3-state propagation time (Z→H)	t _{PZH}	4.5	$R_L=1k\Omega$	1444	8	15		19	ns
		6.0	110/19	9	7	13		16	
		2.0	(0)	1,00	20	75	(1)	95	
3-state propagation time	t _{PZL}	4.5	$R_L=1k\Omega$	177	9	15		19	ns
(Z→L)		6.0	100 100	3° . 6	7	13	V	16	

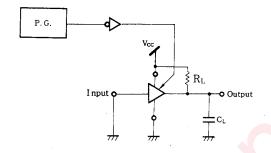
- Switching time measuring circuit and waveforms
 - (1) t_{TLH}, t_{THL}, t_{PLH}, t_{PHL}
 - 1. Measuring circuit

2. Switching waveforms

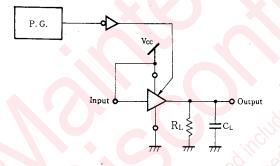




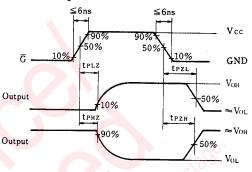
- (2) t_{PHZ} , t_{PZH}
- 1. Measuring circuit



- (3) t_{PLZ} , t_{PZL}
- 1. Measuring circuit



2. Switching waveforms



Switching waveforms
 See above (2) 2 for waveforms.



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